

Resistors

1. Linear resistor

2. Non linear resistor

A-photo resistors

B-thermostats

C-voltage-dependent resistors

1. Linear resistor (obeys ohms law)

$R=I/V$, Ω , $K\Omega$, $M\Omega$

Power rating (wattage) $W=V*I=I^2*R$. (1/8W, 1/4W,.....1)

***-COLOUR CODING**

Color	figure	Tolerance(percent)
Black	0	
BROWN	1	
RED	2	
ORANGE	3	
YELLOW	4	
GREEN	5	
BLUE	6	
VIOLET	7	
GREY	8	
WHITE	9	
SILVER		$\pm\%0$
NONE		$\pm\%20$
GOLD		$\pm\%10$

Resistor Ω = first colour + second colour * 10^{third color} \pm fourth color

$R=18*10^2\pm5\%$

2-CAPACITORS

The ability of capacitor to store energy is called (capacitance)

* capacitance, C = charge Q / charge V , $C = \epsilon A / d$

$C, \mu F = 1 \cdot 10^{-6}$ FARAD

, $n f = 1 \cdot 10^{-9}$ FARAD

$Pf = 1 \cdot 10^{-12}$ FARAD

ϵ = dielectric constant of insulator

A = area of plat

d = distance between two plates

*VOLTAGE RATING

The maximum voltage that can applied between the plates of a capacitor without

*STOED ENERGY IN CAPACITORS

Energy (Joules) = $\frac{1}{2}CV^2$

*TYPES OF CAPACITORS

A-NON-ELECTROLYTIC (not polarized)

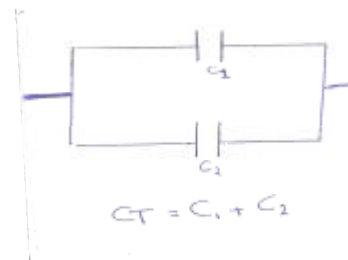
B-ELECTROLYTIC (polarized)

*SERIES CONNECTIONS

$C_t = 1/C_1 + 1/C_2$

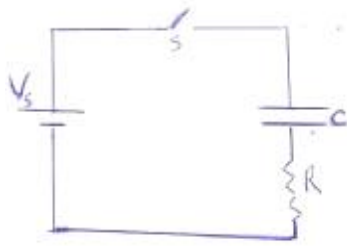
*PARALLED CONNECTION

$C_t = C_1 + C_2$



CHARGING AND DISCHARGING CAPACITOR

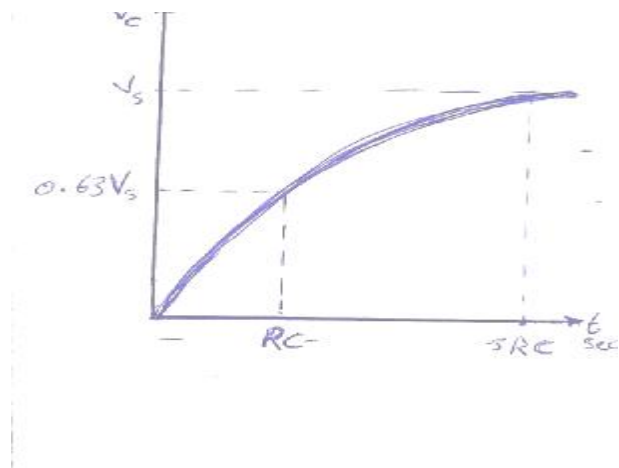
A) - CHARGING CAPACITORS



The capacitor may be charged from a D.C supply (V_s) to a (V_c)

$$V_c = V_s (1 - \exp(-t/RC)) \quad RC = \text{time constant} = (\tau)$$

$$RC = V/I * Q/V = Q/(Q/t) = \text{sec}$$

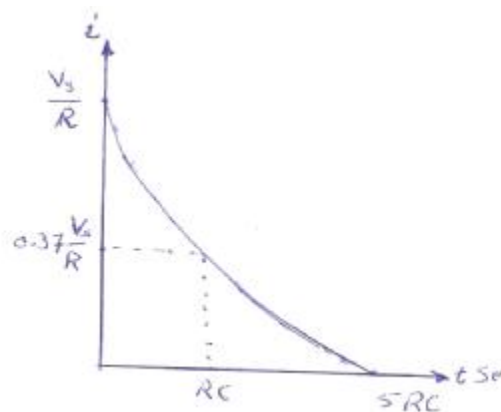


after $t = \tau = RC$

$$V_c = 0.63 V_s$$

$$\text{after } t = \tau = RC \quad V_c \approx V_s$$

B) - CHARGING CURRENT



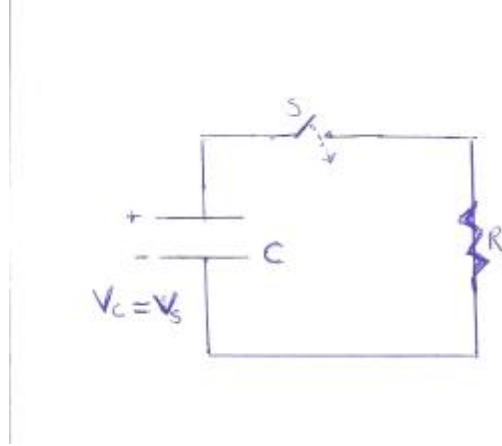
$$I = V_s / R \exp(-t/RC)$$

After $t = \tau = RC$

$$I = 0.37 V_s / R$$

after $t \approx 5RC$ $I \approx 0$

B) DISCHARGING CAPACITOR



After the process to V_s , the discharge will take the form:

$$V_c = V_s \exp(-t/RC)$$

(Voltage across the capacitor)

$$I = V_s / R \exp(-t/RC)$$

(Discharge current in the discharge circuit)

*The discharge & the charge frequency of the circuit is related to the (τ)

$$f_{HZ} = 1/\tau$$

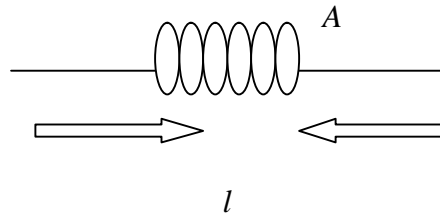
*INDUCTORS & TRANSFORMERS:

1-SELF-INDUCTANCE. Is the property in which e. m. f is produced when a charging current flows in the circuit or component.

$$e. m. f, C = -n (d \Phi / d t) = -L (d I / d t) \dots \text{faraday's law}$$

THES, the self- inductance $L = N (d \Phi / d t)$

$$L = \mu \circ \mu r AN^2 / l \text{ (coil)}$$



Where $\mu_0 \mu_r = \mu$ (permeability of the core).

(μ) is the ability of a material to conduct magnetic flux (permeability)

N is the number of turns of coil

A is the cross sectional area of coil

L is the length of coil

2-MUTUAL INDUCTANCE

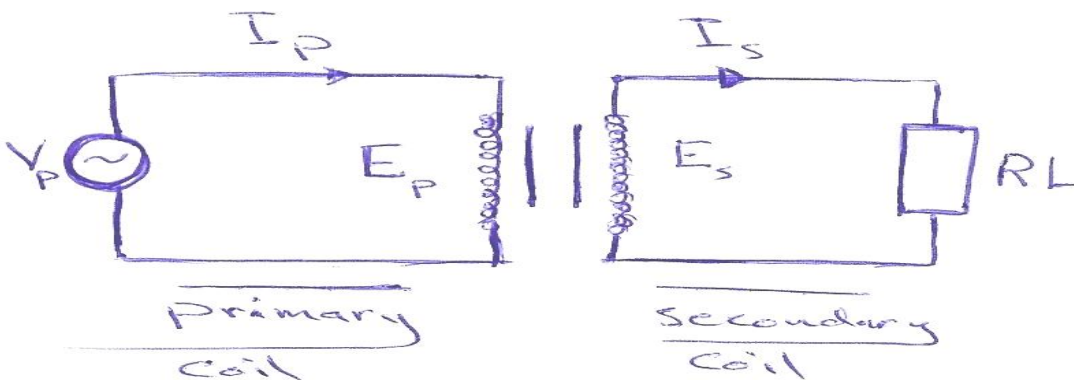
Two circuits are said to possess mutual inductance if a changing current in one circuit gives rise to changing magnetic flux, which links with the second circuit, causing an e. m. f. to be induced in the second coil

3-TRANSFORMERS

The transformers are used either step-up transformer or step down transformer.

***step-up $V_s \uparrow, I_s \downarrow$**

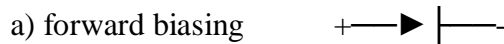
***step-down $V_s \downarrow, I_s \uparrow$**



***transformation ratio, $N = (V_p / V_s) = (N_p / N_s)$
 $= (I_s / I_p)$**

4 - IDEAL DIODE:

The ideal diode, is an open circuit in reverse biasing and is a short circuit in forward biasing



5- REAL DIODE:

1) -CURRENT- VOLTAGE CHARACTERISTICS OF DIODES

*the diode current can be related to the applied Voltage on the temperature with the following equation

$$I_D = I_s (\exp(KV/T) - 1)$$

Where I_s = reverse current saturation

$$K = 11600 / \eta$$

$\eta = 1$ for Ge diode & 2 for Si diode

V = the applied voltage (+) for forward biasing & (-) for reverse biasing

2) - DC OR STATIC RESISTANCE OF DIODE (R_{dc})

$$R_{dc} = V_D / I_D \Omega$$

3) - AC OR DYNAMIC RESISTANCE OF DIODE (R_{AC})

$$R_{AC} = \Delta V_D / \Delta I_D \Omega$$

C) -DIODE SPECIFICATION:

The specifications of semiconductor diode are

1- The maximum forward voltage V_{fmax}

2- The maximum forward current I_{fmax}

3- The maximum reverse current $I_{R \max}$

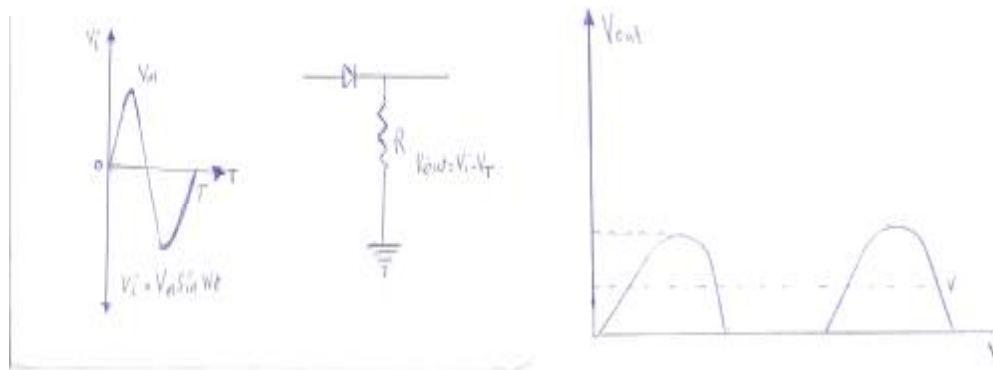
D-Diode applications:

A- half-wave Rectification

B-full-wave Rectification

1- Rectification.

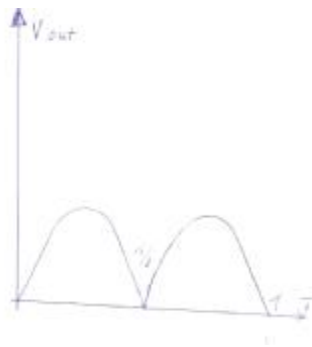
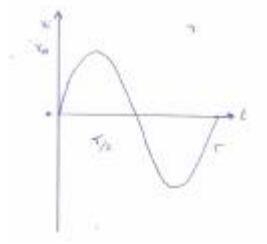
A- half-wave Rectification.



$$V_{d.c} = 0.318 V_m - V_t$$

$$PIV \text{ Rating} = V_m$$

b- full-wave Rectification.



1 – Bridge Rectification

**during the period*

$T = 0 \text{ to } t/2$ $D2, D3$ (short)

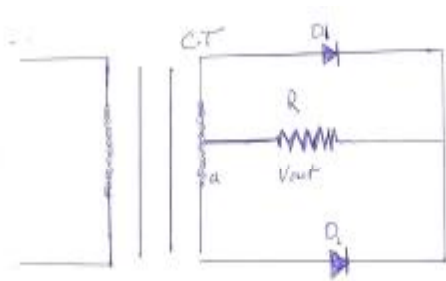
**during the period*

$T = t/2 \text{ to } t$ $D1, D4$ (short)
 $D2, D3$ (open)

$V_{dc} = 0.636 (V_m - 2V_t)$.

$PIV = V_m$

2- full-wave Rectification with center-tapped transformer



* The potential at point (a) = zero (center the secondary coil).

*during the negative port ($0 \rightarrow T/2$) D2 (short)
D 1(open)

*during the positive port ($T/2 \rightarrow T$) D 1(short)
D 2(open)

$$V_{d.c} = 0.636 (V_m - V_t)$$

$$PIV = 2V_m$$

2-Clippers

The diode networks that have the ability "clip" or apportion of the input signal without distorting the remaining part of the alternating wave.

A-Series

b- Parallel

3- Clampers.

The diode network that will "Clamp" a signal to a different DC level

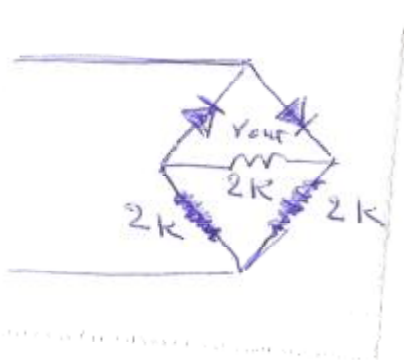
Examples

1- Sketch (V_{out}) for each networks (ideal diode)

A-

B-

2- Determine the **output wave** from for the network



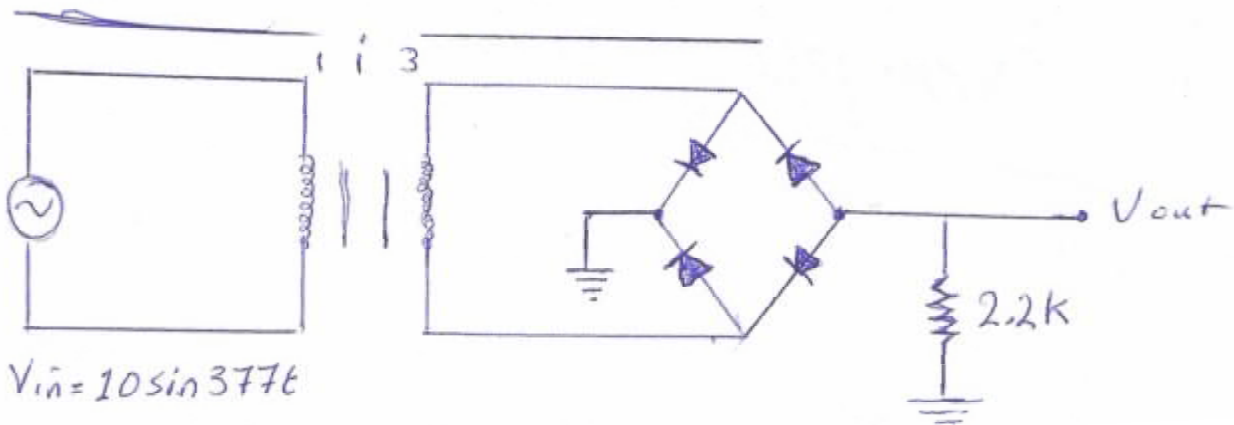
3- A full-wave bridge rectifier with a 20 V r. M.s sinusoidal input has a load resistor of $1\text{ k}\Omega$

a- if silicon diode employed, what is the (**D C**) voltage an available at the load.

b- determine the required **PIV** rating of each diode.

c- Find the maximum current through each diode during conduction

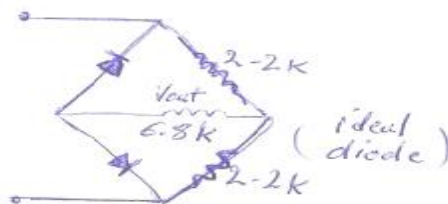
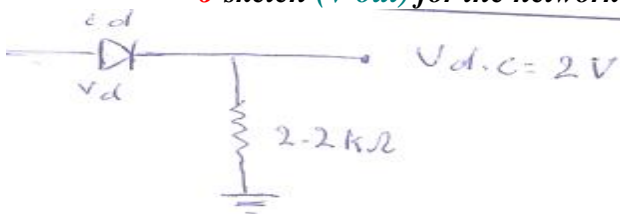
4- Determine (**V out**) and the required **PIV** rating of each diode for the network



5- Assuming an ideal diode, sketch **VI**, **VD** and **Id** for the half-wave rectifier of the figure. The input is a sinusoidal waveform with a frequency of 60 Hz

*repeat (Q5) with a silicon diode ($V_t = 0.7$).

6- sketch (**V out**) for the network of fig and determine the **DC** voltage viable



4-Filtering

The o/p voltage from bridge rectifier or half-wave rectifier is not pure DC voltage to increase the DC component in the o/p wave for a capacitor must be used.

** The pulse period $T = 1/F_{out}$ $F_{out} = 2 F_{in}$*

**for good DC (nearly pure DC) $RLC \geq 10 * T$*

** $V_{DC} = [1 - (0.00417/RLC)] * V_p$*

Where V_{DC} is the o/p DC voltage, V_p is the peak a flow the bridge rectifier

**the ripple voltage*

$$V_r = 0.0024 V_p / RLC \quad r.m.s$$

** The important parameter in Dc power supply.
Is the ripple factor (r)*

$$r = (V_r/V_{DC}) * 100 \%$$

ex: /for the circuit in fig (a) if the $V_p = 30v$, find the V_{DC} and the ripple voltage

ex: /design voltage mode power supply with the following characteristics

A- Output voltage 10V?

b- Output current 1 A?

c- Ripple factor 5%?

